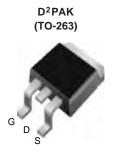
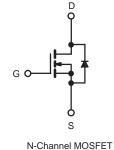




# N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>(BR)DSS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)		
200	0.022 at $V_{GS}$ = 10 V	70		





Top View

#### FEATURES

- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- 100 %  $R_{g}$  and UIS tested

#### **APPLICATIONS**

- LCD/LED TV
- Consumer Appliances
- Lighting
- AC-DC Power Supply

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub>	= 25 °C, unl	less otherwis	se noted)			
PARAMETER			SYMBOL	LIMIT	UNIT	
Drain-Source Voltage			V <sub>DS</sub>	200	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20	v			
Continuous Drain Current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C T <sub>C</sub> = 100 °C	1-	70 <sup>a</sup>		
Continuous Brain Gunent	VGS at 10 V	T <sub>C</sub> = 100 °C	ID	65 <sup>a</sup>	A	
Pulsed Drain Current			I <sub>DM</sub>	280		
Single Pulse Avalanche Energy			E <sub>AS</sub>	165	mJ	
Avalanche Current			I <sub>AR</sub>	68	A	
Repetiitive Avalanche Energy			E <sub>AR</sub>	24	mJ	
Maximum Power Dissipation	$T_{C} = 25 \text{ °C}$ $T_{A} = 25 \text{ °C}^{b}$		P <sub>D</sub>	375	w	
				3.1 <sup>c</sup>		
Peak Diode Recovery dV/dt			dV/dt	5.0	V/ns	
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature) for 10 s			Ŭ	300	C	

THERMAL RESISTANCE RATINGS							
PARAMETER	SYMBOL	TYP.	MAX.	UNIT			
Maximum Junction-to-Ambient (PCB Mounted, Steady-State)	R <sub>thJA</sub>	-	35	°C/W			
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	-	0.45				

a. Package limited.

b. When Mounted on 1" square PCB (FR-4 material).

c. See SOA curve for voltage derating.

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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS}=0~V,~I_D=250~\mu A$	200	-	-	V		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},\ I_{D}=250\ \mu A$	2	-	4	v		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V},  V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA		
	I <sub>DSS</sub>	$V_{DS} = 160 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	μA		
Zero Gate Voltage Drain Current		$V_{DS} = 160 \; V,  V_{GS} = 0 \; V,  T_J = 125 \; ^{\circ}C$	-	-	100			
		$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	2	mA		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \geq 10$ V, $V_{GS}$ = 10 V	25	-	-	А		
Drain-Source On-State Resistance <sup>a</sup>	в	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	-	0.022	0.032	.032 Ω		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 25 A	-	0.027	0.039	32		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 20 \text{ V}, I_D = 30 \text{ A}$	-	15	-	S		
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		-	5050	-			
Output Capacitance	Coss	$V_{GS}$ = 0 V, $V_{DS}$ = 100 V, f = 1 MHz		450		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	90	-			
Total Gate Charge <sup>c</sup>	Qg		-	90	130			
Gate-Source Charge c	Q <sub>gs</sub>	$V_{DS}$ = 100 V, $V_{GS}$ = 10 V, $I_{D}$ = 30 A		25		nC		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			33				
Gate Resistance	Rg	f = 1 MHz		3.9		Ω		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			15	26	ns		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 100 V, R <sub>L</sub> = 1.67 $\Omega$		25	44			
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D\cong$ 30 A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		27	54			
Fall Time <sup>c</sup>	t <sub>f</sub>		-	9	20			
Drain-Source Body Diode Ratings an	d Characteris	stics <sup>b</sup> (T <sub>C</sub> = 25 °C)						
Pulsed Current (t = 100 µs)	I <sub>SM</sub>		-	-	280	А		
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{F} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		0.75	1.5	V		
Reverse Recovery Time	t <sub>rr</sub>		-	88	176	ns		
Peak Reverse Recovery Charge	IRM(REC)	$I_F = 20 \text{ A}, \text{ d}/\text{dt} = 100 \text{ A}/\mu\text{s}$	-	5	10	А		
Reverse Recovery Charge	Q <sub>rr</sub>			0.22	0.44	μC		

#### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

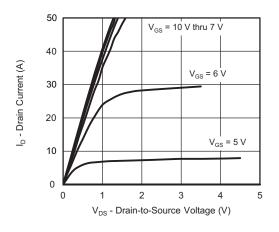
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

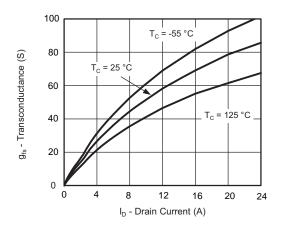
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



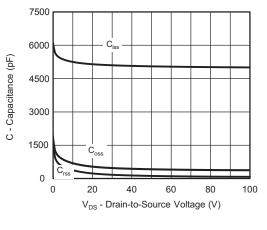
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



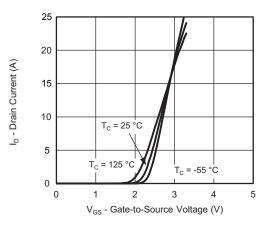
**Output Characteristics** 



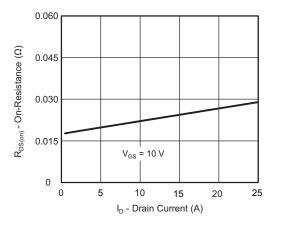
Transconductance



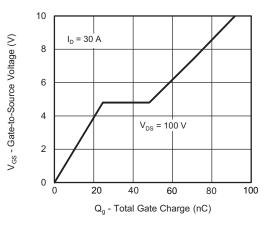
Capacitance



**Transfer Characteristics** 



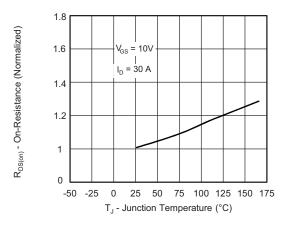
**On-Resistance vs. Drain Current** 



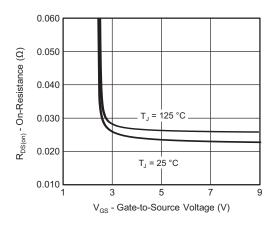
**Gate Charge** 



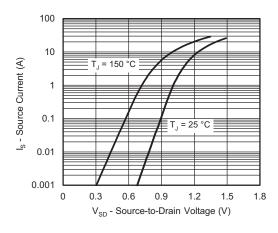
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



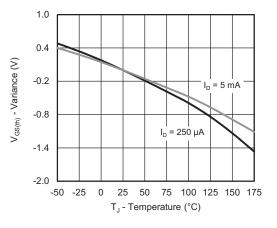
**On-Resistance vs. Junction Temperature** 



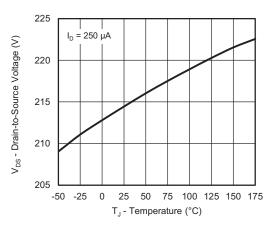
On-Resistance vs. Gate-to-Source Voltage



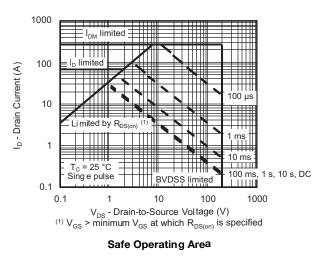
Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature





### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

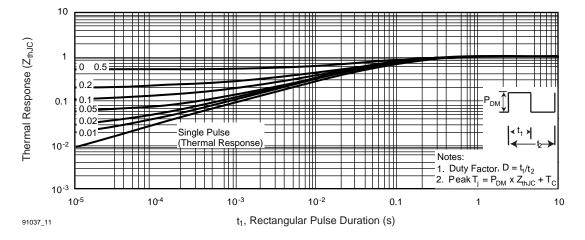
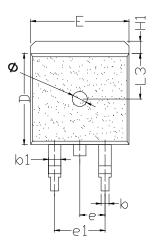


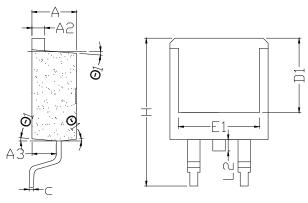
Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

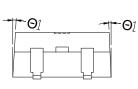


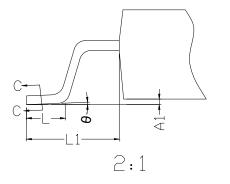
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# TO-263 PACKAGE OUTLINE









#### COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
А	4.10	4.50	4.80	е	2.35	2.54	2.75
A1	0.00	0.10	0.30	e1	5.08REF		
A2	1.10	1.30	1.50	Н	14.50	15.15	16.00
A3	2.15	2.50	3.10	H1	1.00	1.28	1.75
b	0.60	0.80	1.05	L	1.80	2.23	2.90
b1	1.05	1.33	1.50	L1	4.30	4.75	5.50
С	0.33	0.50	0.66	L2	1.00	1.30	1.85
D	8.40	9.20	9.60	L3	0.90	4.65	9.00
D1	7.50REF			ф	0°	2°	5°
E	9.60	10.02	10.80	φ1	2°	-	7°
E1	7.60	9.88	10.30	Φ		1.5BSC	



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